

**Amendment to the Title:**

Please amend the title as follows:

METHODS OF FORMING A PHOSPHORUS DOPED  
~~SILICON DIOXIDE COMPRISING~~ SILICON DIOXIDE-  
COMPRISING LAYER

**Amendments to the Specification:**

Please amend paragraph [0004] as follows:

[0004] This invention includes methods of forming a ~~phosphorus~~ phosphorus doped silicon dioxide comprising layers, and methods of forming trench isolation in the fabrication of integrated circuitry. In one implementation, a method of forming a phosphorus doped silicon dioxide comprising layer includes positioning a substrate within a deposition chamber. First and second vapor phase reactants are introduced in alternate and temporally separated pulses to the substrate within the chamber in a plurality of deposition cycles under conditions effective to deposit a phosphorus doped silicon dioxide comprising layer on the substrate. One of the first and second vapor phase reactants is  $\text{PO}(\text{OR})_3$  where R is hydrocarbyl, and an other of the first and second vapor phase reactants is  $\text{Si}(\text{OR})_3\text{OH}$  where R is hydrocarbyl.